# Silicon Carbide (SiC) MOSFET - EliteSiC, 32 mohm, 650 V, M3S, TO247-4L

*Preliminary Document*

# NTH4LN032N065M3S

| $V_{(BR)DSS}$ | $R_{DS(ON)}$ TYP | $I_D$ MAX |
|---|---|---|
| 650 V | 32 mΩ @ 18 V | 50 A |

### Features

- Typical $R_{DS(ON)}$ = 32 mΩ @ $V_{GS}$ = 18 V
- Ultra Low Gate Charge ($Q_{G(tot)}$ = 55 nC)
- High Speed Switching with Low Capacitance ($C_{oss}$ = 114 pF)
- 100% Avalanche Tested
- This Device is Halide Free and RoHS Compliant with exemption 7a, Pb-Free 2LI (on second level interconnection)

### Applications

- SMPS, Solar Inverters, UPS, Energy Storage, EV Charging Infrastructure

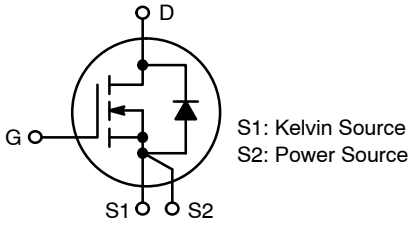
**MAXIMUM RATINGS** ($T_J$ = 25 °C unless otherwise noted)

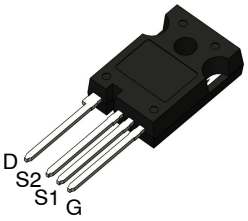
| Parameter | | Symbol | Value | Unit |
|---|---|---|---|---|
| Drain-to-Source Voltage | | $V_{DSS}$ | 650 | V |
| Gate-to-Source Voltage | | $V_{GS}$ | −8/+22 | V |
| Continuous Drain Current | $T_C$ = 25 °C | $I_D$ | 50 | A |
| Power Dissipation | | $P_D$ | 187 | W |
| Continuous Drain Current (Note 1) | $T_C$ = 100 °C | $I_D$ | 30 | A |
| Power Dissipation | | $P_D$ | 94 | W |
| Pulsed Drain Current (Note 2) | $T_C$ = 25 °C, $t_p$ = 100 μs | $I_{DM}$ | 163 | A |
| Continuous Source-Drain Current (Body Diode) | $T_C$ = 25 °C, $V_{GS}$ = −3 V | $I_S$ | 29 | A |
| | $T_C$ = 100 °C, $V_{GS}$ = −3 V | | 16 | |
| Pulsed Source-Drain Current (Body Diode) (Note 2) | $T_C$ = 25 °C, $V_{GS}$ = −3 V, $t_p$ = 100 μs | $I_{SM}$ | 137 | A |
| Single Pulse Avalanche Energy ($I_{LPK}$ = 16.7 A, L = 1 mH) (Note 3) | | $E_{AS}$ | 139 | mJ |
| Operating Junction and Storage Temperature Range | | $T_J$, $T_{stg}$ | −55 to +175 | °C |
| Lead Temperature for Soldering Purposes (1/8″ from case for 10 secs) | | $T_L$ | 270 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. 30 A is limited by package. Power chip max drain current is 35 A if limited by max junction temperature.
2. Single pulse, limited by max junction temperature.
3. $E_{AS}$ of 139 mJ is based on starting $T_J$ = 25 °C, L=1 mH, $I_{AS}$=16.7 A, $V_{DD}$ = 100 V, $V_{GS}$ = 18 V.

**N-CHANNEL MOSFET**




**TO-247-4L**
**CASE 340CW**

**MARKING DIAGRAM**


4LN032065M3S = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
ZZ = Lot Traceability

**ORDERING INFORMATION**

| Device | Package | Shipping |
|---|---|---|
| NTH4LN032N065M3S | TO-247-4L | 30 Units / Tube |

This Preliminary document is for informational purposes only. **onsemi** may update or withdraw it without notice. Content and referenced products are under development and subject to change.

## THERMAL CHARACTERISTICS

| Parameter | Symbol | Value | Unit |
|---|---|---|---|
| Thermal Resistance, Junction-to-Case (Note 4) | $R_{\theta JC}$ | 0.80 | °C/W |
| Thermal Resistance, Junction-to-Ambient (Note 4) | $R_{\theta JA}$ | 40 | |

4. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

## RECOMMENDED OPERATING CONDITIONS

| Parameter | Symbol | Value | Unit |
|---|---|---|---|
| Operation Values of Gate-to-Source Voltage | $V_{GSop}$ | −5...−3/+18 | V |

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

## ELECTRICAL CHARACTERISTICS ($T_J$ = 25 °C unless otherwise specified)

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| **OFF CHARACTERISTICS** | | | | | | |
| Drain-to-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS}$ = 0 V, $I_D$ = 1 mA, $T_J$ = 25 °C | 650 | – | – | V |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$ = 650 V, $T_J$ = 25 °C | – | – | 10 | μA |
| | | $V_{DS}$ = 650 V, $T_J$ = 175 °C (Note 6) | – | – | 500 | μA |
| Gate-to-Source Leakage Current | $I_{GSS}$ | $V_{GS}$ = −8/+22 V, $V_{DS}$ = 0 V | – | – | ±1.0 | μA |
| **ON CHARACTERISTICS** | | | | | | |
| Drain-to-Source On Resistance | $R_{DS(on)}$ | $V_{GS}$ = 18 V, $I_D$ = 15 A, $T_J$ = 25 °C | – | 32 | – | mΩ |
| | | $V_{GS}$ = 18 V, $I_D$ = 15 A, $T_J$ = 175 °C (Note 6) | – | 49 | – | |
| | | $V_{GS}$ = 15 V, $I_D$ = 15 A, $T_J$ = 25 °C | – | 41 | – | |
| | | $V_{GS}$ = 15 V, $I_D$ = 15 A, $T_J$ = 175 °C (Note 6) | – | 52 | – | |
| Gate Threshold Voltage | $V_{GS(TH)}$ | $V_{GS}$ = $V_{DS}$, $I_D$ = 7.5 mA, $T_J$ = 25 °C | – | 2.7 | – | V |
| Forward Transconductance | $g_{FS}$ | $V_{DS}$ = 10 V, $I_D$ = 15 A (Note 6) | – | 9.9 | – | S |
| **CHARGES, CAPACITANCES & GATE RESISTANCE** | | | | | | |
| Input Capacitance | $C_{ISS}$ | $V_{DS}$ = 400 V, $V_{GS}$ = 0 V, f = 1 MHz (Note 6) | – | 1410 | – | pF |
| Output Capacitance | $C_{OSS}$ | | – | 114 | – | |
| Reverse Transfer Capacitance | $C_{RSS}$ | | – | 9.2 | – | |
| Total Gate Charge | $Q_{G(TOT)}$ | $V_{DD}$ = 400 V, $I_D$ = 15 A, $V_{GS}$ = −3/18 V (Note 6) | – | 55 | – | nC |
| Gate-to-Source Charge | $Q_{GS}$ | | – | 15 | – | |
| Gate-to-Drain Charge | $Q_{GD}$ | | – | 14 | – | |
| Gate Resistance | $R_G$ | f = 1 MHz | – | 5.0 | – | Ω |
| **SWITCHING CHARACTERISTICS** | | | | | | |
| Turn-On Delay Time | $t_{d(ON)}$ | $V_{GS}$ = −3/18 V, $V_{DD}$ = 400 V, $I_D$ = 15 A, $R_G$ = 4.7 Ω, $T_J$ = 25 °C (Notes 5, 6) | – | 8.8 | – | ns |
| Turn-Off Delay Time | $t_{d(OFF)}$ | | – | 31 | – | |
| Rise Time | $t_r$ | | – | 12 | – | |
| Fall Time | $t_f$ | | – | 9 | – | |
| Turn-On Switching Loss | $E_{ON}$ | | – | 33 | – | μJ |
| Turn-Off Switching Loss | $E_{OFF}$ | | – | 16 | – | |
| Total Switching Loss | $E_{TOT}$ | | – | 49 | – | |

**ELECTRICAL CHARACTERISTICS** ($T_J$ = 25 °C unless otherwise specified) (continued)

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| **SWITCHING CHARACTERISTICS** | | | | | | |
| Turn-On Delay Time | $t_{d(ON)}$ | $V_{GS}$ = −3/18 V, $V_{DD}$ = 400 V, $I_D$ = 15 A, $R_G$ = 4.7 Ω, $T_J$ = 175 °C (Notes 5, 6) | – | 7.8 | – | ns |
| Turn-Off Delay Time | $t_{d(OFF)}$ | | – | 37 | – | |
| Rise Time | $t_r$ | | – | 12 | – | |
| Fall Time | $t_f$ | | – | 11 | – | |
| Turn-On Switching Loss | $E_{ON}$ | | – | 31 | – | μJ |
| Turn-Off Switching Loss | $E_{OFF}$ | | – | 25 | – | |
| Total Switching Loss | $E_{TOT}$ | | – | 56 | – | |
| **SOURCE-TO-DRAIN DIODE CHARACTERISTICS** | | | | | | |
| Forward Diode Voltage | $V_{SD}$ | $I_{SD}$ = 15 A, $V_{GS}$ = −3 V, $T_J$ = 25 °C | – | 4.5 | – | V |
| | | $I_{SD}$ = 15 A, $V_{GS}$ = −3 V, $T_J$ = 175 °C (Note 6) | – | 4.2 | – | |
| Reverse Recovery Time | $t_{RR}$ | $V_{GS}$ = −3 V, $I_S$ = 15 A, dI/dt = 1000 A/μs, $V_{DS}$ = 400 V (Note 6) | – | 15.5 | – | ns |
| Charge Time | $t_a$ | | – | 8.9 | – | |
| Discharge Time | $t_b$ | | – | 6.6 | – | |
| Reverse Recovery Charge | $Q_{RR}$ | | – | 72 | – | nC |
| Reverse Recovery Energy | $E_{REC}$ | | – | 4.6 | – | μJ |
| Peak Reverse Recovery Current | $I_{RRM}$ | | – | 9.3 | – | A |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. $E_{ON}/E_{OFF}$ result is with body diode.
6. Defined by design, not subject to production test.

## TYPICAL CHARACTERISTICS

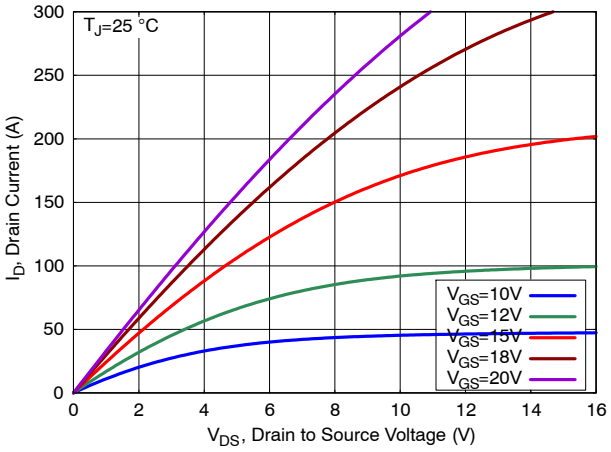



**Figure 1. On-Region Characteristics**

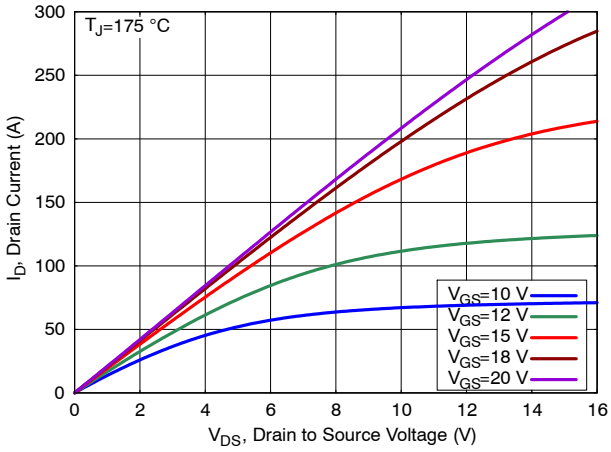



**Figure 2. Output Characteristics**

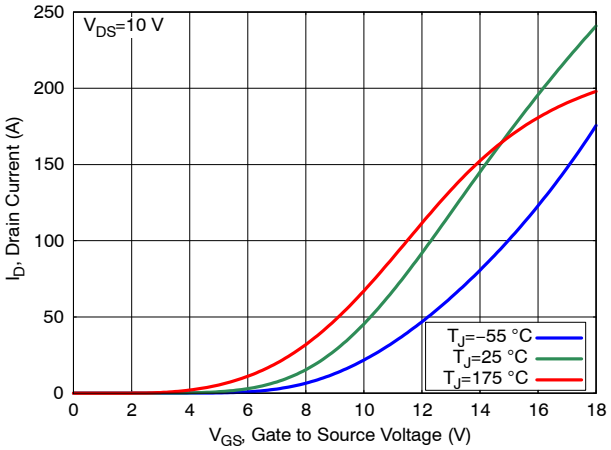



**Figure 3. Transfer Characteristics**

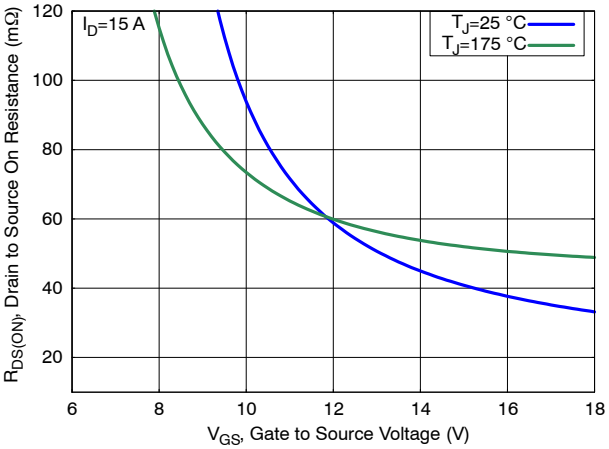



**Figure 4. On-Resistance vs. Gate Voltage**

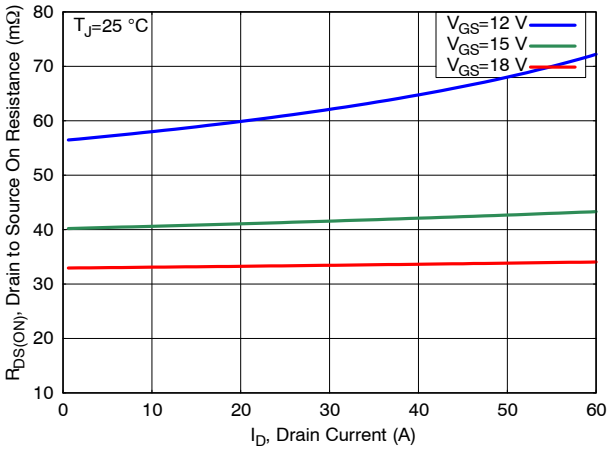



**Figure 5. On-Resistance vs. Drain Current**

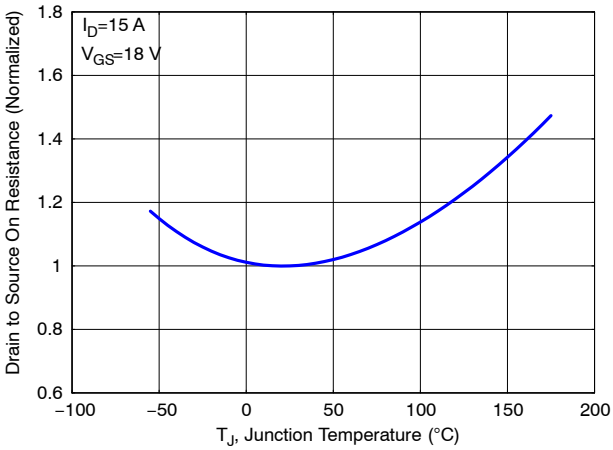



**Figure 6. On-Resistance vs. Junction Temperature**

## TYPICAL CHARACTERISTICS

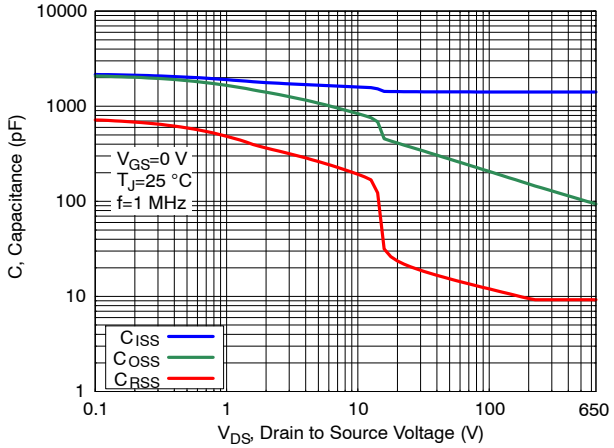



**Figure 7. Capacitance Characteristics**

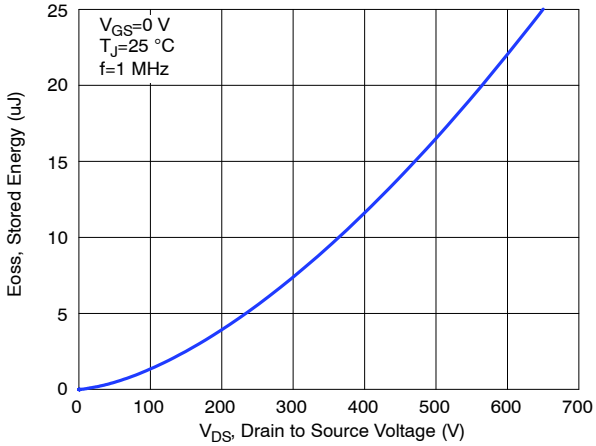



**Figure 8. Stored Energy vs. Drain-to-Source Voltage**

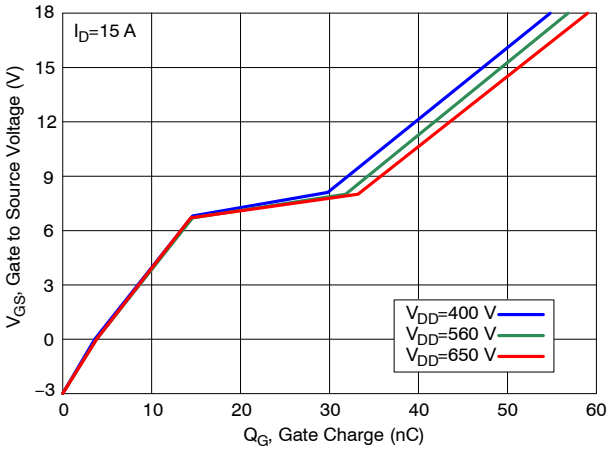



**Figure 9. Gate Charge Characteristics**

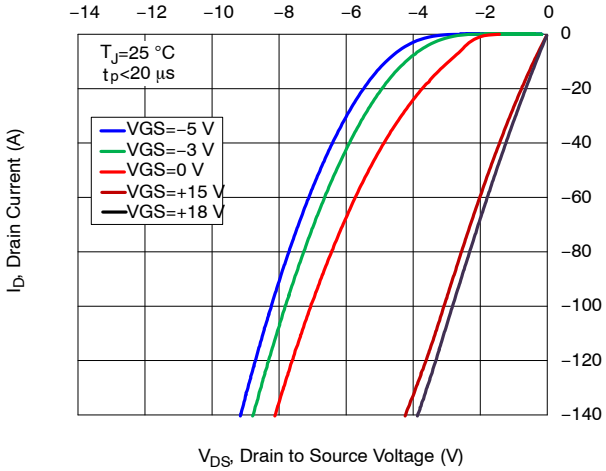



**Figure 10. Reverse Conduction Characteristics**

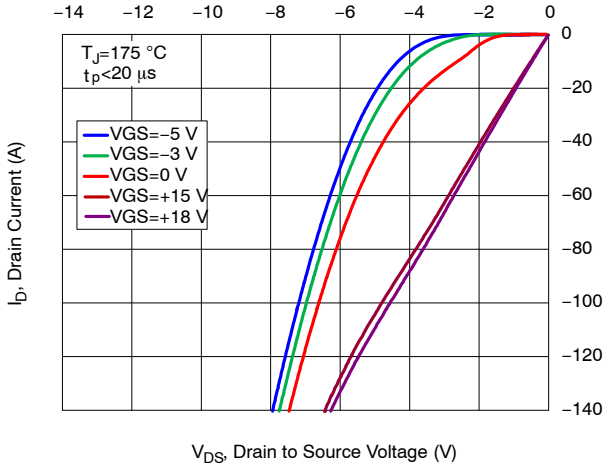



**Figure 11. Reverse Conduction Characteristics**

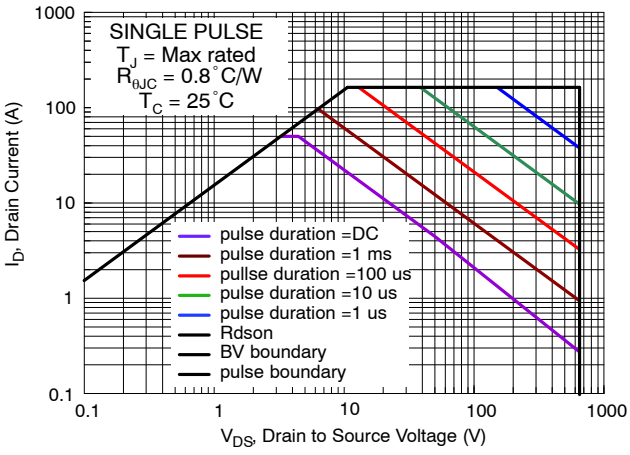



**Figure 12. Safe Operating Area**

## TYPICAL CHARACTERISTICS

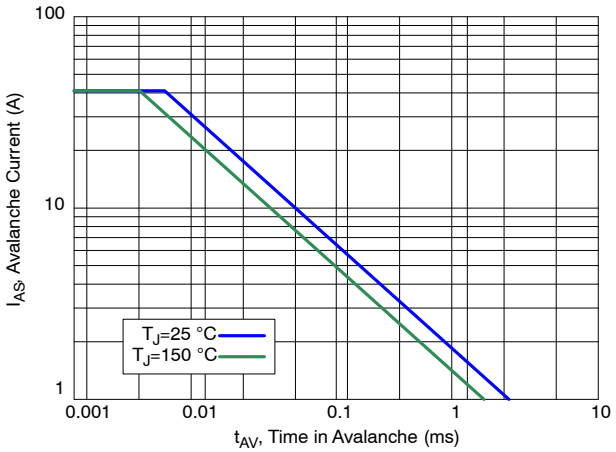



**Figure 13. Avalanche Current vs. Pulse Time (UIS)**

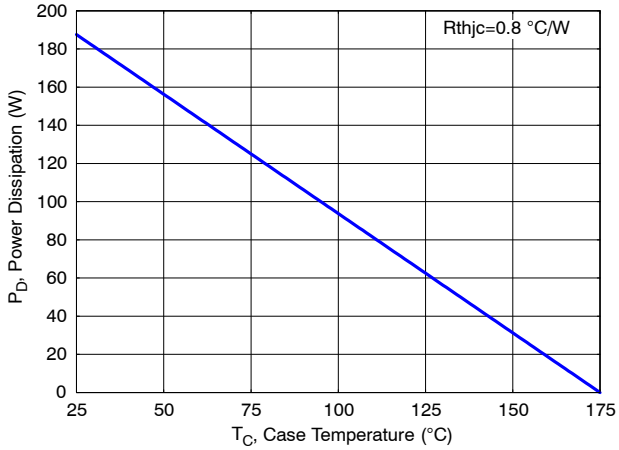



**Figure 14. Maximum Power Dissipation vs. Case Temperature**

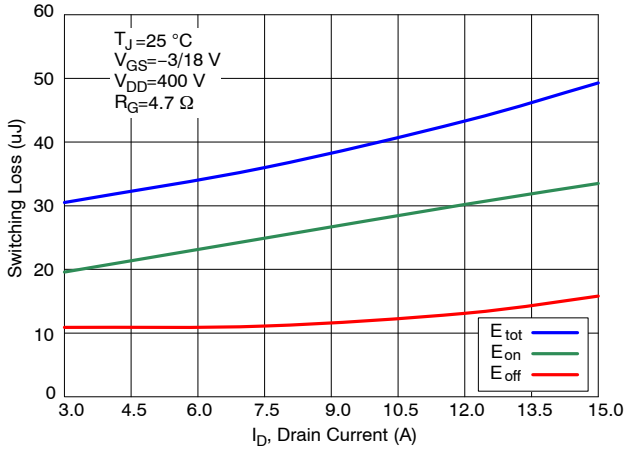



**Figure 15. Inductive Switching Loss vs. Drain Current**

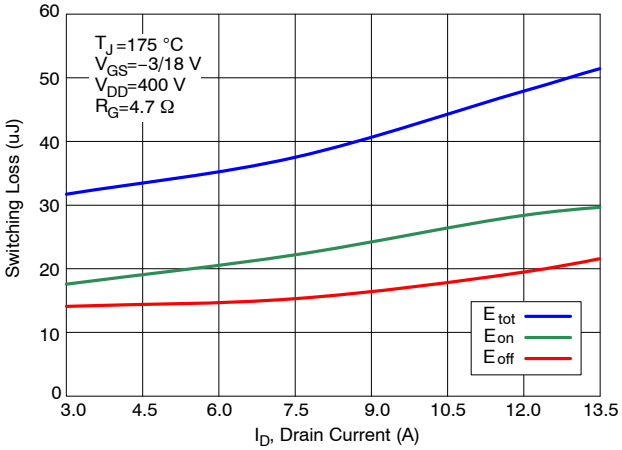



**Figure 16. Inductive Switching Loss vs. Drain Current**

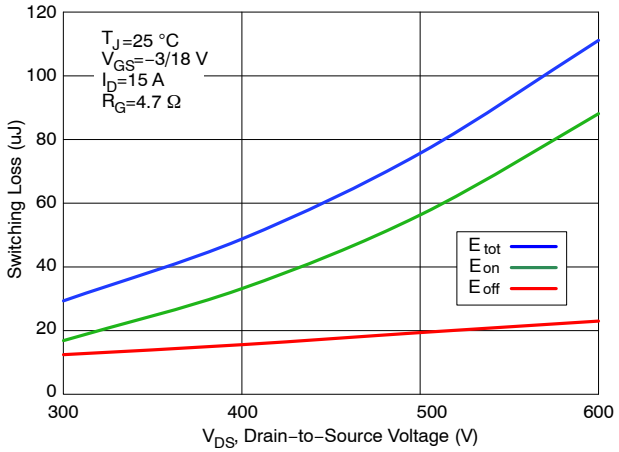



**Figure 17. Inductive Switching Loss vs. Drain Voltage**

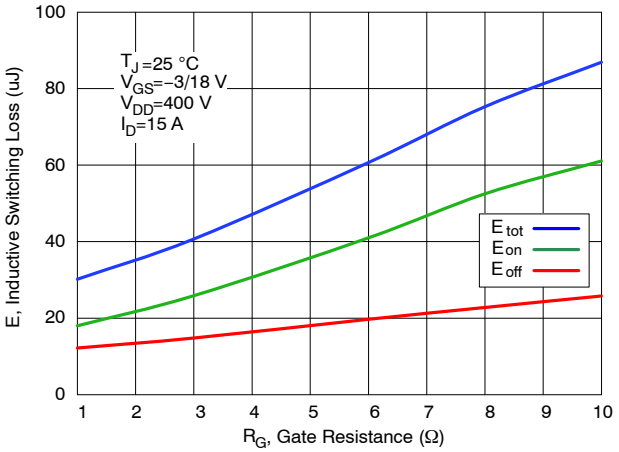



**Figure 18. Inductive Switching Loss vs. Gate Resistance**

## TYPICAL CHARACTERISTICS

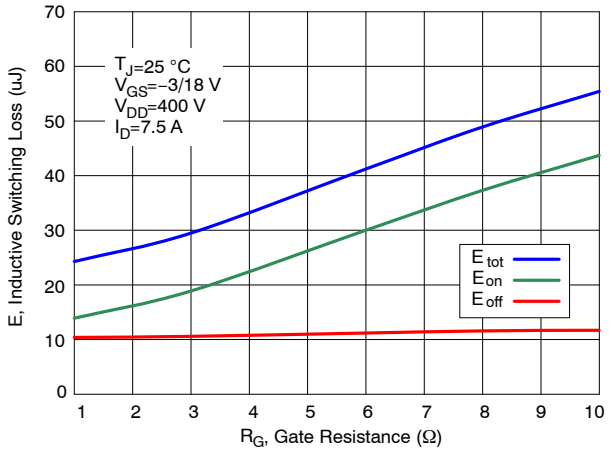



**Figure 19. Inductive Switching Loss vs. Gate Resistance**

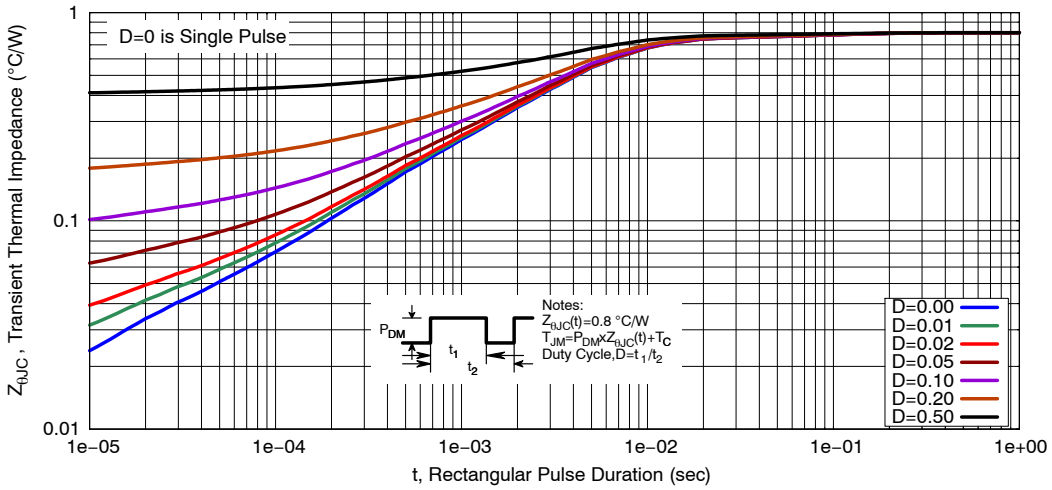
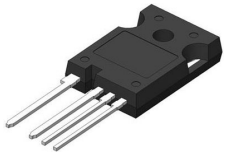



**Figure 20. Thermal Response Characteristics**

## REVISION HISTORY

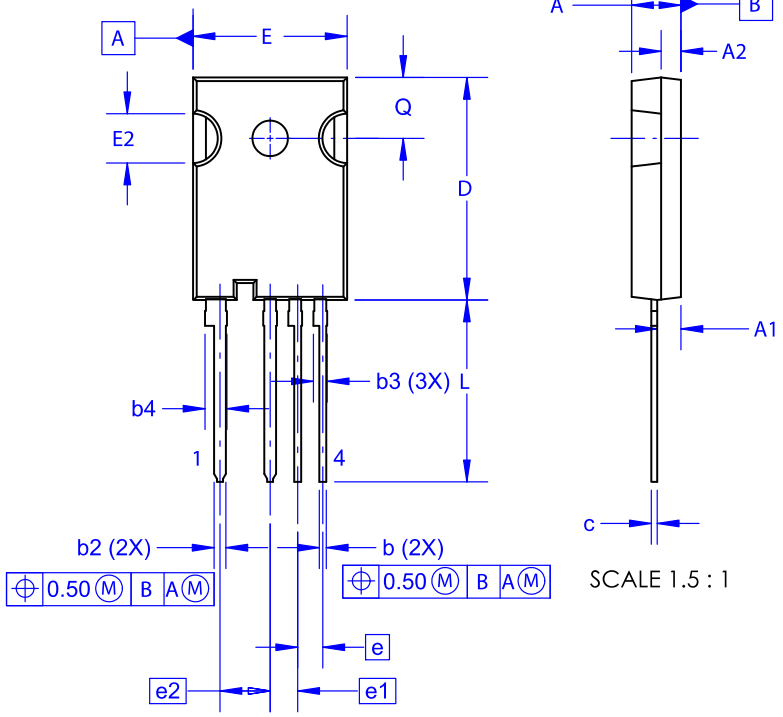
| Revision | Description of Changes | Date |
|---|---|---|
| P0 | Initial Preliminary document release. | 5/28/2026 |

## PACKAGE DIMENSIONS



**TO−247 4−LEAD, THIN LEADS**
CASE 340CW
ISSUE A

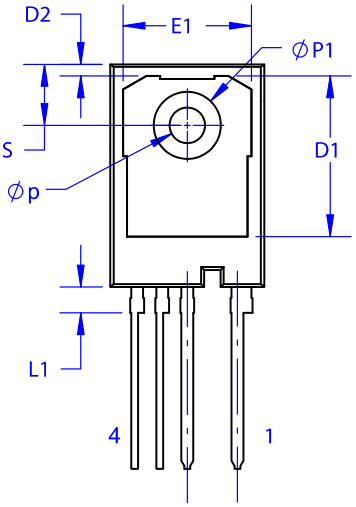
DATE 16 SEP 2019




SCALE 1.5 : 1




SCALE 1.5 : 1




SCALE 1.5 : 1

NOTES:

A. NO INDUSTRY STANDARD APPLIES TO THIS PACKAGE.
B. DIMENSIONS ARE EXCLUSIVE OF BURRS,MOLD FLASH AND TIE BAR EXTRUSIONS.
C. ALL DIMENSIONS ARE IN MILLIMETERS.

| DIM | MILLIMETERS | | |
|---|---|---|---|
| | MIN | NOM | MAX |
| A | 4.80 | 5.00 | 5.20 |
| A1 | 2.10 | 2.40 | 2.70 |
| A2 | 1.80 | 2.00 | 2.20 |
| b | 0.57 | 0.70 | 0.83 |
| b2 | 1.07 | 1.20 | 1.33 |
| b3 | 1.20 | 1.40 | 1.60 |
| b4 | 2.02 | 2.22 | 2.42 |
| c | 0.50 | 0.60 | 0.70 |
| D | 22.34 | 22.54 | 22.74 |
| D1 | 16.00 | 16.30 | 16.50 |
| D2 | 0.97 | 1.17 | 1.37 |
| e | | 2.54 | |
| e1 | | 2.79 | |
| e2 | | 5.08 | |
| E | 15.40 | 15.60 | 15.80 |
| E1 | 12.80 | 13.00 | 13.20 |
| E2 | 4.80 | 5.00 | 5.20 |
| L | 18.12 | 18.42 | 18.72 |
| L1 | 2.42 | 2.62 | 2.82 |
| Øp | 3.40 | 3.60 | 3.80 |
| ØP1 | 6.60 | 6.80 | 7.00 |
| Q | 5.97 | 6.17 | 6.37 |
| S | 5.97 | 6.17 | 6.37 |

## ADDITIONAL INFORMATION

**TECHNICAL PUBLICATIONS**:
**Technical Library:** www.onsemi.com/design/resources/technical−documentation
**onsemi Website:** www.onsemi.com

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**For additional information, please contact your local Sales Representative at** www.onsemi.com/support/sales